

4.0A Sensitive Gate SCRs

Product Summary

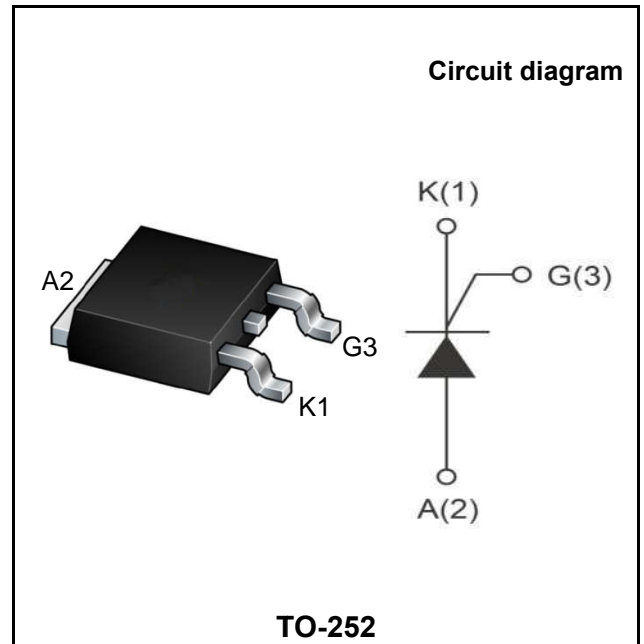
Symbol	Value	Unit
$I_{T(RMS)}$	4.0	A
$V_{DRM} V_{RRM}$	600/800	V
I_{GT}	200	μA

Features

With high ability to withstand the shock loading of large current, Provide high dv/dt rate with strong resistance to electromagnetic interference.

Application

Power charger, T-tools, massager, solid state relay, AC Motor speed regulation and so on.



Order Information

Part Number	Package	Marking	Delivery Form	Delivery Quantity
X0405D	TO-252	X0405 600 XXXX	12" T&R	2500PCS/Tape

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	V_{DRM}	600/800	V
Repetitive peak reverse voltage	V_{RRM}	600/800	V
RMS on-state current	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	30	A
I^2t value for fusing (tp=10ms)	I^2t	4.5	A^2s
Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$)	di_T/dt	50	$A/\mu s$
Peak gate current	I_{GM}	1.2	A
Average gate power dissipation	$P_G (AV)$	0.2	W
Junction Temperature	T_J	-40~+110	°C
Storage Temperature	T_{STG}	-40 ~+150	°C

Electrical characteristics (TA=25°C, unless otherwise noted)

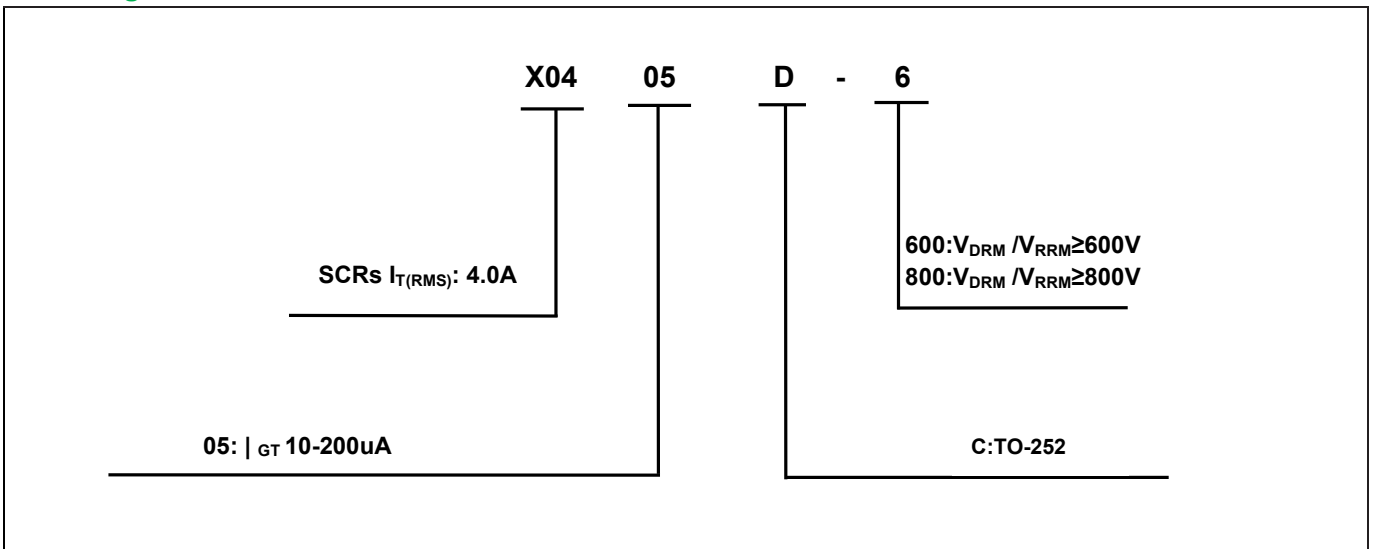
Parameter	Symbol	Test Condition	Value		Unit
			Min	Max	
Gate trigger current	I_{GT}	$V_D = 12V R_L = 140\Omega T_j = 25^\circ C$	10	200	μA
Gate trigger voltage	V_{GT}		-	0.8	V
Gate non-trigger voltage	V_{GD}	$V_D = V_{DRM} R_{GK} = 1k\Omega T_j = 110^\circ C$	0.2	-	V
latching current	I_L	$I_G = 1mA R_{GK} = 1k\Omega T_j = 25^\circ C$	-	6	mA
Holding current	I_H	$I_T = 50mA R_{GK} = 1k\Omega T_j = 25^\circ C$	-	5	mA
Critical-rate of rise of commutation voltage	dV_D/dt	$V_D = 2/3V_{DRM} R_{GK} = 1k\Omega T_j = 110^\circ C$	10	-	V/ μs

STATIC CHARACTERISTICS

Forward "on" voltage	V_{TM}	$I_{TM} = 8A t_p = 380\mu s$	-	1.55	V	
Repetitive Peak Off-State Current	I_{DRM}	$V_D = V_{DRM} V_R = V_{RRM}$	$T_j = 25^\circ C$	-	5	μA
Repetitive Peak Reverse Current	I_{RRM}		$T_j = 110^\circ C$	-	0.15	mA

THERMAL RESISTANCES

Thermal resistance	$R_{th(j-c)}$	Junction to case (AC)	TYP.	7.2	$^\circ C/W$
	$R_{th(j-a)}$	Junction to ambient	TYP.	100	$^\circ C/W$

Ordering Information


Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

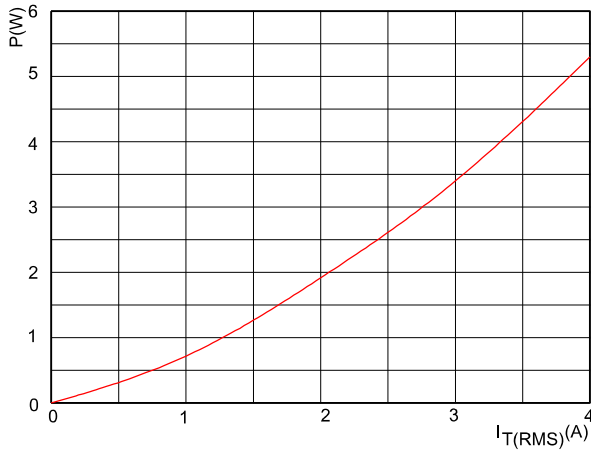


FIG.2: RMS on-state current versus case temperature (full cycle)

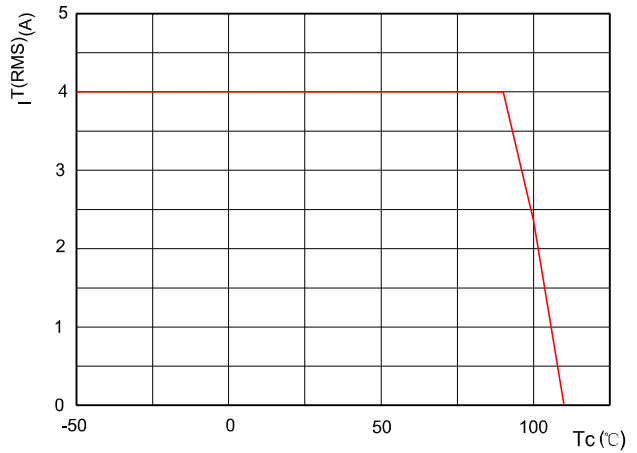


FIG.3: Surge peak on-state current versus number of cycles

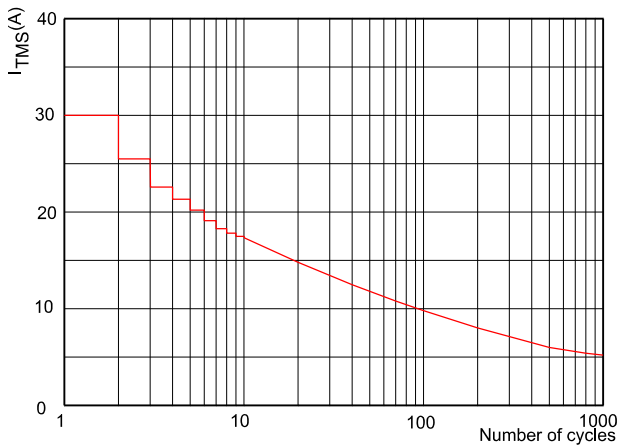


FIG.4: On-state characteristics (maximum values)

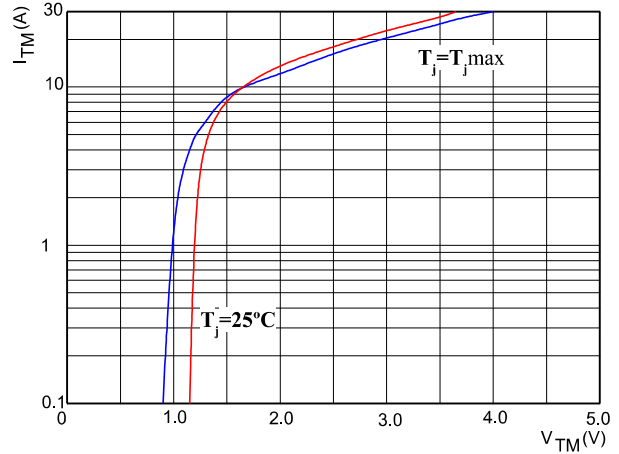


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$

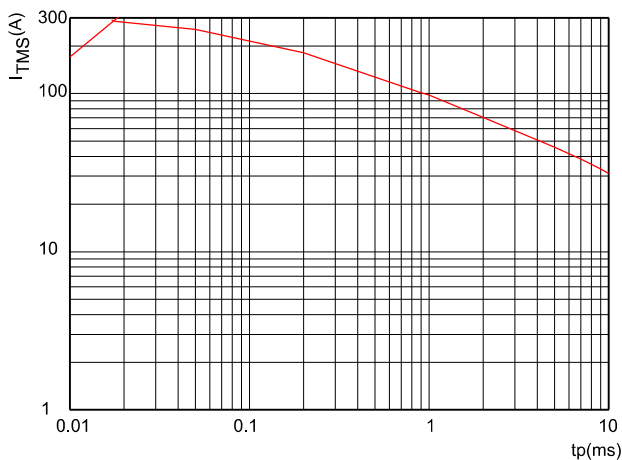
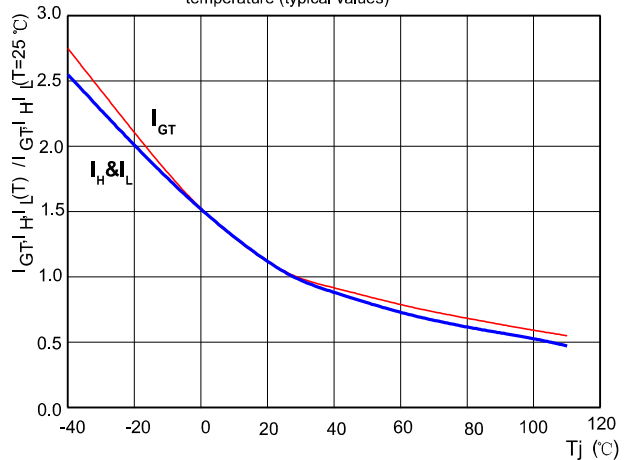
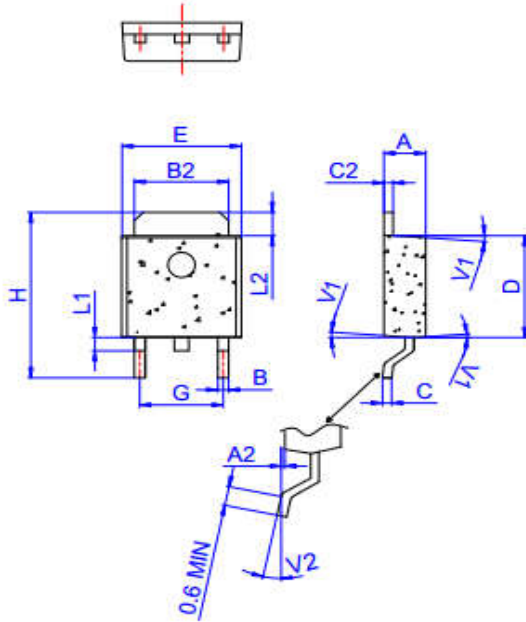


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.85	0.019		0.034
D	5.30		6.20	0.208		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°